

RFM12N08/12N10 RFP12N08/12N10

N-Channel Enhancement Mode
Power Field Effect Transistors

August 1991

Features

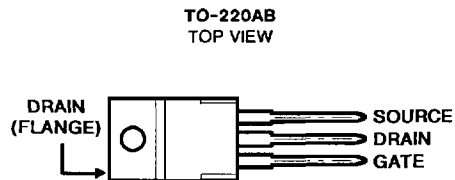
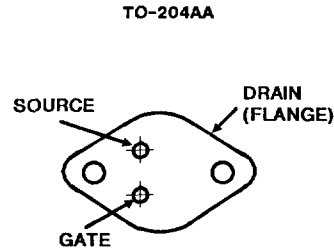
- 12A, 80V and 100V
- $r_{DS(on)} = 0.2\Omega$
- SOA is Power-Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device

Description

The RFM12N08 and RFM12N10 and the RFP12N08 and RFP12N10 are n-channel enhancement-mode silicon-gate power field-effect transistors designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high-power bipolar switching transistors requiring high speed and low gate-drive power. These types can be operated directly from integrated circuits.

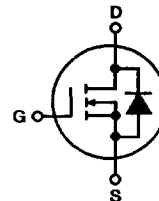
The RFM-series types are supplied in the JEDEC TO-204AA steel package and the RFP-series types in the JEDEC TO-220AB plastic package.

Packages



Terminal Diagram

N-CHANNEL ENHANCEMENT MODE



Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$), Unless Otherwise Specified

	RFM12N08	RFM12N10	RFP12N08	RFP12N10	UNITS	
Drain-Source Voltage	V_{DS}	80	100	80	100	V
Drain-Gate Voltage ($R_{GS} = 1\text{m}\Omega$)	V_{DGR}	80	100	80	100	V
Continuous Drain Current						
RMS Continuous	I_D	12	12	12	12	A
Pulsed Drain Current	I_{DM}	30	30	30	30	A
Gate-Source Voltage	V_{GS}	± 20	± 20	± 20	± 20	V
Maximum Power Dissipation						
$T_C = +25^\circ\text{C}$	P_D	75	75	60	60	W
Above $T_C = +25^\circ\text{C}$, Derate Linearly		0.6	0.6	0.48	0.48	W/ $^\circ\text{C}$
Operating and Storage Junction	T_J, T_{STG}	-55 to +150	-55 to +150	-55 to +150	-55 to +150	$^\circ\text{C}$
Temperature Range						

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N-CHANNEL
POWER MOSFETS

Specifications RFM12N08, RFM12N10, RFP12N08, RFP12N10

ELECTRICAL CHARACTERISTICS, At Case Temperature (T_c)=25°C unless otherwise specified

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	LIMITS				UNITS
			RFM12N08 RFP12N08		RFM12N10 RFP12N10		
			Min.	Max.	Min.	Max.	
Drain Source Breakdown Voltage	BV_{DSS}	$I_D=1\text{ mA}$ $V_{GS}=0$	80	—	100	—	V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}$ $I_D=1\text{ mA}$	2	4	2	4	V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=65\text{ V}$	—	1	—	—	μA
		$V_{DS}=80\text{ V}$	—	—	—	1	
		$T_c=125^\circ\text{ C}$ $V_{DS}=65\text{ V}$ $V_{DS}=80\text{ V}$	—	50	—	—	
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20\text{ V}$ $V_{DS}=0$	—	100	—	100	nA
Drain-Source On Voltage	$V_{DS(on)}^a$	$I_D=6\text{ A}$ $V_{GS}=10\text{ V}$	—	1.2	—	1.2	V
		$I_D=12\text{ A}$ $V_{GS}=10\text{ V}$	—	3.3	—	3.3	
Static Drain-Source On Resistance	$r_{DS(on)}^a$	$I_D=6\text{ A}$ $V_{GS}=10\text{ V}$	—	0.2	—	0.2	Ω
Forward Transconductance	g_{fs}^a	$V_{DS}=10\text{ V}$ $I_D=6\text{ A}$	2	—	2	—	mho
Input Capacitance	C_{iss}	$V_{DS}=25\text{ V}$	—	850	—	850	pF
Output Capacitance	C_{oss}	$V_{GS}=0\text{ V}$	—	300	—	300	
Reverse-Transfer Capacitance	C_{rss}	$f=1\text{ MHz}$	—	150	—	150	
Turn-On Delay Time	$t_d(on)$	$V_{DD}=50\text{ V}$	45(Typ)	70	45(Typ)	70	ns
Rise Time	t_r	$I_D=6\text{ A}$	250(Typ)	375	250(Typ)	375	
Turn-Off Delay Time	$t_d(off)$	$R_{\theta gn}=R_{\theta gs}=50\ \Omega$	85(Typ)	130	85(Typ)	130	
Fall Time	t_f	$V_{GS}=10\text{ V}$	100(Typ)	150	100(Typ)	150	
Thermal Resistance Junction-to-Case	$R_{\theta jc}$	RFM12N08, RFM12N10	—	1.67	—	1.67	
		RFP12N08, RFP12N10	—	2.083	—	2.083	

^aPulsed: Pulse duration=300 μs max., duty cycle=2%.

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	LIMITS				UNITS
			RFM12N08 RFM12N10		RFP12N08 RFP12N10		
			MIN.	MAX.	MIN.	MAX.	
Diode Forward Voltage	V_{SD}	$I_{SD}=6\text{ A}$	—	1.4	—	1.4	V
Reverse Recovery Time	t_{rr}	$I_F=4\text{ A}$ $d_{IF}/d_t=100\text{ A}/\mu\text{s}$	150(typ)		150(typ)		ns

*Pulse Test: Width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

RFM12N08, RFM12N10, RFP12N08, RFP12N10

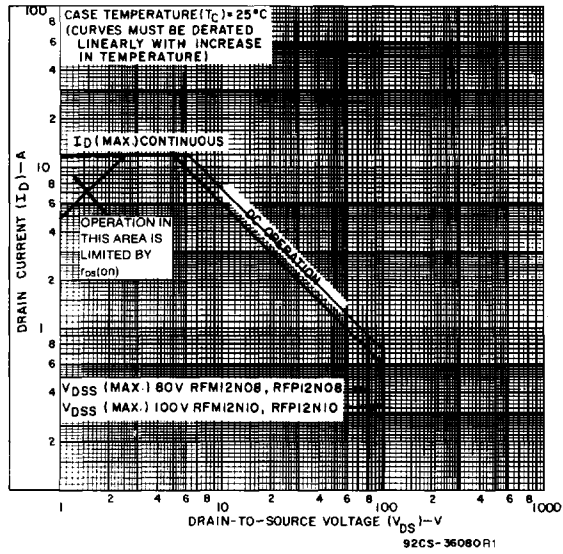


Fig. 1 - Maximum operating areas for all types.

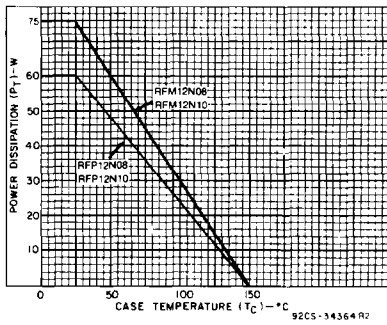


Fig. 2 - Power dissipation vs. temperature derating curve for all types.

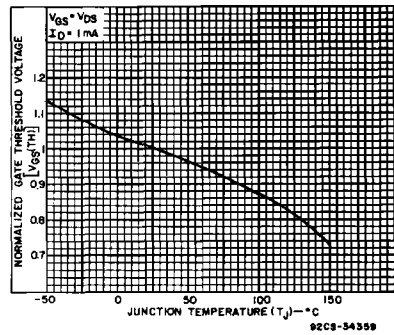


Fig. 3 - Typical normalized gate threshold voltage as a function of junction temperature for all types.

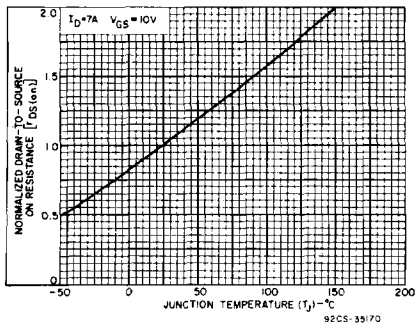


Fig. 4 - Normalized drain-to-source on resistance to junction temperature for all types.

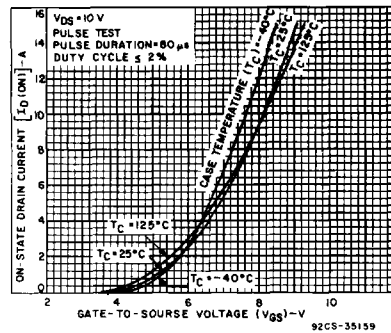


Fig. 5 - Typical transfer characteristics for all types.

RFM12N08, RFM12N10, RFP12N08, RFP12N10

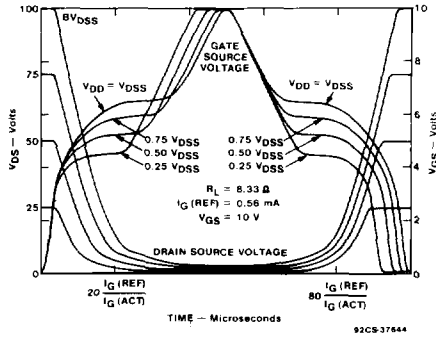


Fig. 6 - Normalized switching waveforms for constant gate-current. Refer to Harris application notes AN-7254 and AN-7260

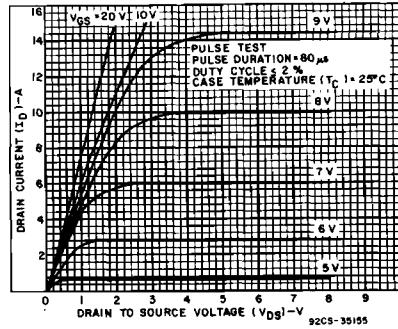


Fig. 7 - Typical saturation characteristics for all types.

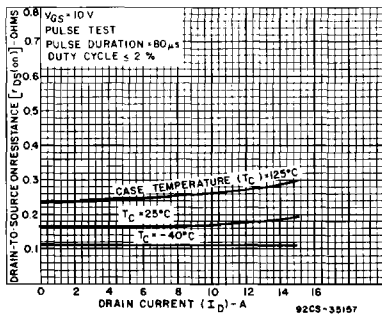


Fig. 8 - Typical drain-to-source on resistance as a function of drain current for all types.

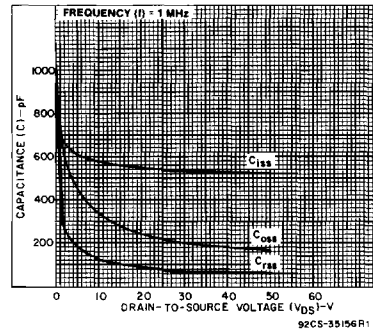


Fig. 9 - Capacitance as a function of drain-to-source voltage for all types.

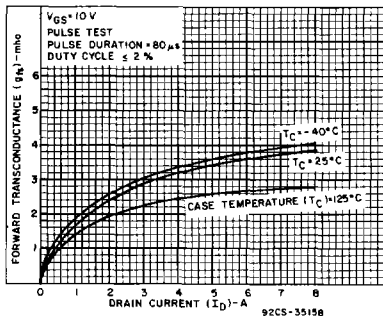


Fig. 10 - Typical forward transconductance as a function of drain current for all types.

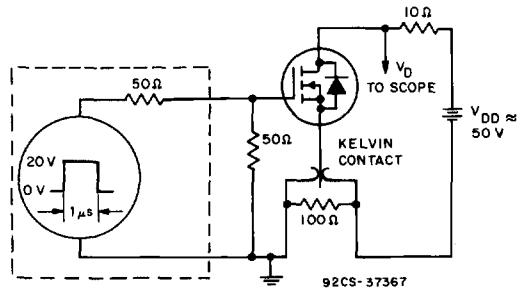


Fig. 11 - Switching Time Test Circuit